



03500.01363

PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of:

MASAAKI IWANE ET AL.

Application No.: 09/346,678

Filed: July 2, 1999

For: CRYSTAL GROWTH PROCESS,
SEMICONDUCTOR DEVICE,
AND ITS PRODUCTION
PROCESS

Examiner: J. Diaz

Group Art Unit: 2815

April 25, 2002

#21 / Pre
C
5/1/02
Smith

Commissioner for Patents
Washington, D.C. 20231

PRELIMINARY AMENDMENT

Sir:

Prior to examination, please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend Claims 7 and 9 to read as follows:

7. (Amended) A semiconductor device comprising a substrate and formed thereon an active layer having the surface of (111)-plane; the active layer being used in photoelectric conversion.